

# XN0F256

## Silicon NPN epitaxial planar type

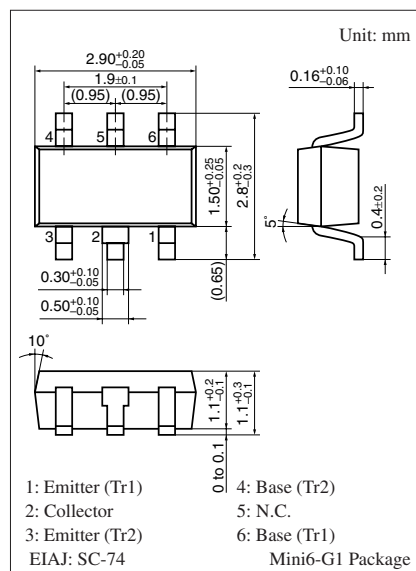
For muting

### ■ Features

- Two elements incorporated into one package  
(Collector-coupled transistors with built-in resistor)
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Reduction of the mounting area and assembly cost by one half

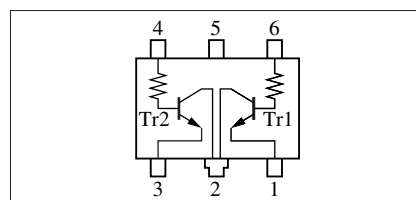
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	30	V
Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	600	mA
Total power dissipation	$P_T$	300	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 6A

Internal Connection

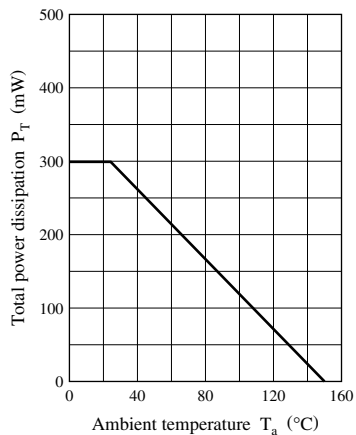


### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

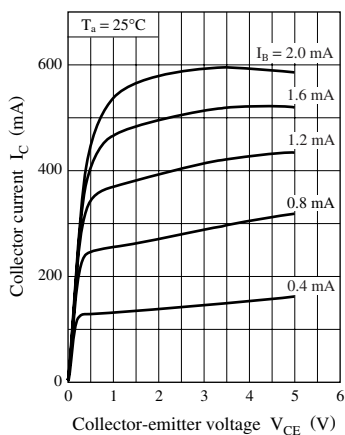
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 1\ \mu\text{A}$ , $I_E = 0$	30			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1\ \text{mA}$ , $I_B = 0$	20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 1\ \mu\text{A}$ , $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 30\ \text{V}$ , $I_E = 0$			1	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 5\ \text{V}$ , $I_C = 0$			1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 5\ \text{V}$ , $I_C = 50\ \text{mA}$	100		600	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\ \text{mA}$ , $I_B = 2.5\ \text{mA}$			80	mV
Input resistance	$R_i$		-30%	4.7	+30%	k $\Omega$
Transition frequency	$f_T$	$V_{CB} = 10\ \text{V}$ , $I_E = -50\ \text{mA}$ , $f = 200\ \text{MHz}$		200		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

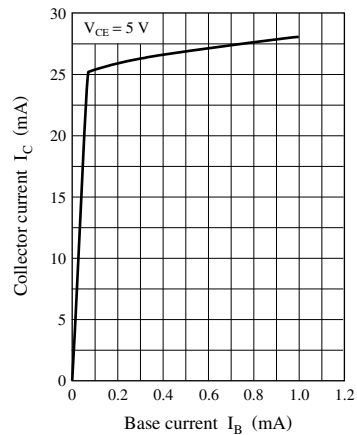
$P_T - T_a$



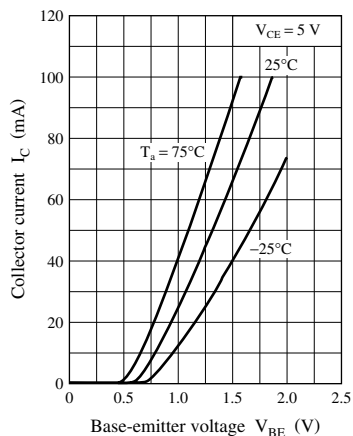
$I_C - V_{CE}$



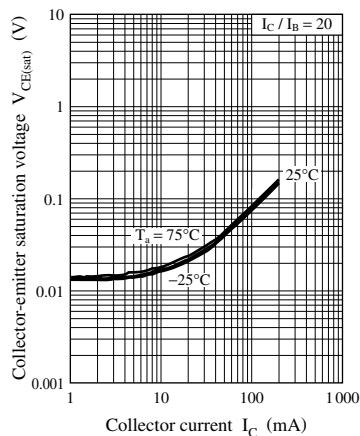
$I_C - I_B$



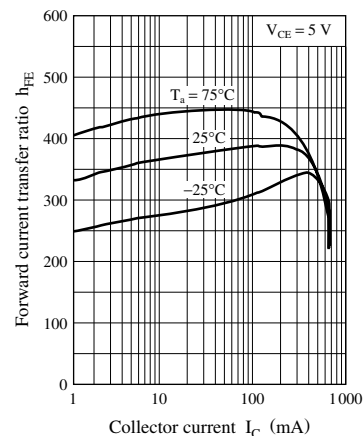
$I_C - V_{BE}$



$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



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